

FNB80460T3

Motion SPM[®] 8 Series

FNB80460T3 is a Motion SPM 8 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, inter-lock function, over-current shutdown, thermal monitoring of drive IC, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's robust shortcircuit-rated IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.

Features

- UL Certified No. E209204 (UL1557)
- 600 V – 4 A 3-Phase IGBT Inverter Including Control IC for Gate Drive and Protections
- Low-Loss, Short-Circuit Rated IGBTs
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Active-high Interface, works with 3.3 / 5 V Logic, Schmitt-trigger Input
- HVIC for Gate Driving, Under-Voltage and Short-Circuit Current Protection
- Fault Output for Under-Voltage and Short-Circuit Current Protection
- Inter-Lock Function to Prevent Short-Circuit
- Shut-Down Input
- HVIC Temperature-Sensing Built-In for Temperature Monitoring
- Isolation Rating: 1500 V_{rms} / min.

Applications

- Motion Control – Home Appliance / Industrial Motor

Related Resources

- [AN-9112](#) – Smart Power Module, Motion SPM 8 Series User's Guide
- AN-9584 – SPM 8 Package Assembly Guidance for 25L double DIP

Integrated Power Functions

- 600 V – 4 A IGBT Inverter for Three Phase DC / AC Power Conversion (Please refer to Figure 2)

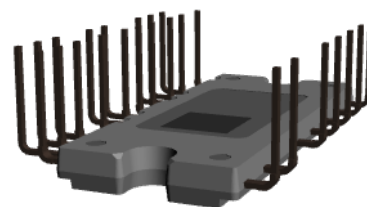
Integrated Drive, Protection and System Control Functions

- For Inverter High-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting control circuit Under-Voltage Lock-Out (UVLO) protection (Note: Available bootstrap circuit example is given in Figures 4 and 16)



ON Semiconductor[®]

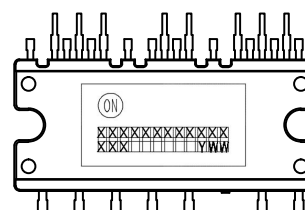
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3D Package Drawing
(Click to Activate 3D Content)

**SPMFA-A25
CASE MODEZ**

MARKING DIAGRAM



ON	= ON Semiconductor Logo
NB80460T3	= Specific Device Code
XXX	= Lot Number
Y	= Year
WW	= Work Week

ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

FNB80460T3

- Control Circuit Under-Voltage Lock-Out (UVLO) protection
- For Inverter Low-side IGBTs: gate drive circuit, Over Current Protection(OCP), Short-Circuit Protection (SCP) control supply circuit Under-Voltage Lock-Out (UVLO) protection
- Fault Signaling: corresponding to UVLO (low-side supply) and SC faults
- Input Interface: High-active interface, works with 3.3 / 5 V logic, Schmitt trigger input

PIN CONFIGURATION

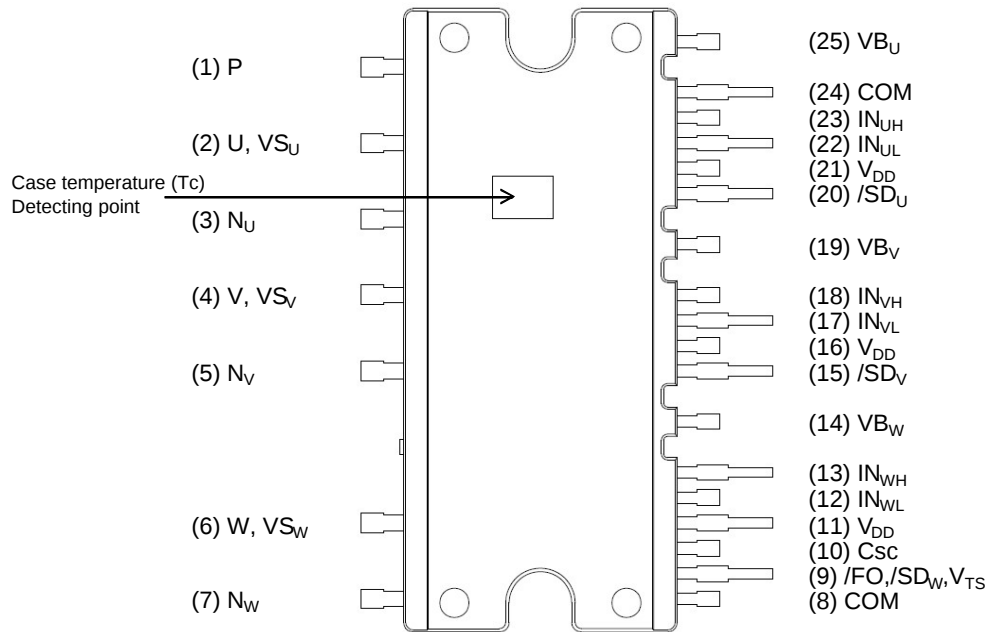


Figure 1. Pin Configuration – Top View

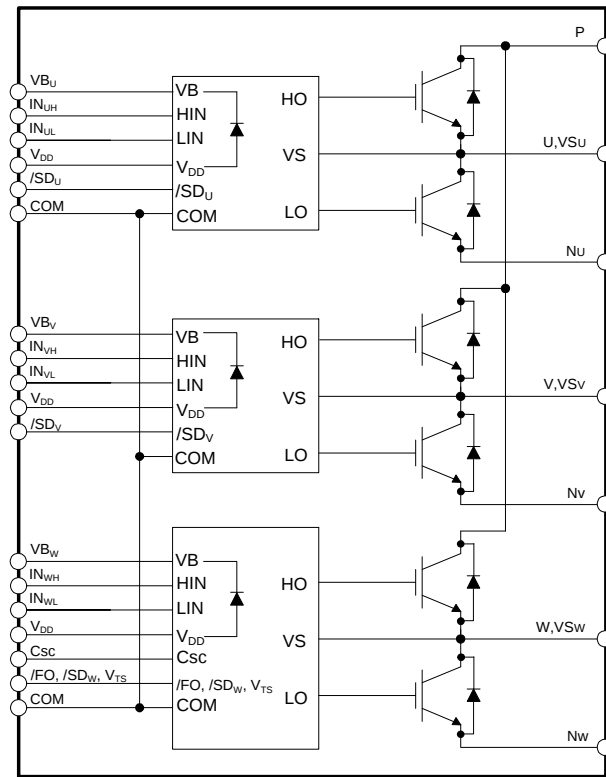
Table 1. PIN DESCRIPTIONS

Pin Number	Pin Name	Pin Description
1	P	Positive DC-Link Input
2	U, VS _U	Output for U Phase
3	N _U	Negative DC-Link Input for U Phase
4	V, VS _V	Output for V Phase
5	N _V	Negative DC-Link Input for V Phase
6	W, VS _W	Output for W Phase
7	N _W	Negative DC-Link Input for W Phase
8	COM	Common Supply Ground
9	/FO, /SD _W , V _{TS}	Fault Output, Shut-Down Input for W Phase, Temperature Output of Drive IC
10	Csc	Shut Down Input for Over Current and Short Circuit Protection
11	V _{DD}	Common Bias Voltage for IC and IGBTs Driving
12	IN _{WL}	Signal Input for Low-Side W Phase
13	IN _{WH}	Signal Input for High-Side W Phase

Table 1. PIN DESCRIPTIONS

Pin Number	Pin Name	Pin Description
14	VB _W	High-Side Bias Voltage for W-Phase IGBT Driving
15	/SD _V	Shut-Down Input for V Phase
16	V _{DD}	Common Bias Voltage for IC and IGBTs Driving
17	IN _{VL}	Signal Input for Low-Side V Phase
18	IN _{VH}	Signal Input for High-Side V Phase
19	VB _V	High-Side Bias Voltage for V-Phase IGBT Driving
20	/SD _U	Shut-Down Input for U Phase
21	V _{DD}	Common Bias Voltage for IC and IGBTs Driving
22	IN _{UL}	Signal Input for Low-Side U Phase
23	IN _{UH}	Signal Input for High-Side U Phase
24	COM	Common Supply Ground
25	VB _U	High-Side Bias Voltage for U-Phase IGBT Driving

INTERNAL EQUIVALENT CIRCUIT AND INPUT/OUTPUT PINS



Notes:

1. Inverter high-side is composed of three IGBTs, freewheeling diodes.
2. Inverter low-side is composed of three IGBTs, freewheeling diodes.
3. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.

Figure 2. Internal Block Diagram

Table 2. ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Rating	Unit
INVERTER PART				
V_{PN}	Supply Voltage	Applied between P – N_U , N_V , N_W	450	V
$V_{PN(\text{Surge})}$	Supply Voltage (Surge)	Applied between P – N_U , N_V , N_W	500	V
V_{CES}	Collector – Emitter Voltage		600	V
$\pm I_C$	Each IGBT Collector Current	$T_C = 25^\circ\text{C}$, $T_J \leq 150^\circ\text{C}$ (Note 1)	4	A
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	$T_C = 25^\circ\text{C}$, $T_J \leq 150^\circ\text{C}$, Under 1 ms Pulse Width (Note 1)	8	A
T_J	Operating Junction Temperature		$-40 \sim 150$	$^\circ\text{C}$
CONTROL PART				
V_{DD}	Control Supply Voltage	Applied between V_{DD} – COM	20	V
V_{BS}	High-Side Control Bias Voltage	Applied between V_{BU} – VS_U , V_{BV} – VS_V , V_{BW} – VS_W	20	V
V_{IN}	Input Signal Voltage	Applied between IN_{UH} , IN_{VH} , IN_{WH} , IN_{UL} , IN_{VL} , IN_{WL} – COM	$-0.3 \sim V_{DD} + 0.3$	V
V_{FS}	Function Supply Voltage	Applied between $/FO$, $/SD_W$, V_{TS} – COM	$-0.3 \sim V_{DD} + 0.3$	V
I_{FO}	Fault Current	Sink Current at $/FO$, $/SD_W$, V_{TS} pin	2	mA
V_{SC}	Current Sensing Input Voltage	Applied between C_{SC} – COM	$-0.3 \sim V_{DD} + 0.3$	V
TOTAL SYSTEM				
$V_{PN(\text{PROT})}$	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{DD} = V_{BS} = 13.5 \sim 16.5 \text{ V}$, $T_J = 150^\circ\text{C}$, Non-Repetitive, $< 2 \mu\text{s}$	400	V
T_{STG}	Storage Temperature		$-40 \sim 125$	$^\circ\text{C}$
V_{ISO}	Isolation Voltage Connect Pins to Heat Sink Plate	AC 60 Hz, Sinusoidal, AC 1 Minute, Connection Pins to Heat Sink Plate	1600	Vrms

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These values had been made an acquisition by the calculation considered to design factor.

Table 3. THERMAL RESISTANCE

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-c)Q}$	Junction-to-Case Thermal Resistance (Note 2)	Inverter IGBT part, (Per Module)	–	–	3.65	$^\circ\text{C/W}$
$R_{th(j-c)F}$		Inverter FWDi part, (Per Module)	–	–	4.13	$^\circ\text{C/W}$

2. For the measurement point of case temperature (T_C), please refer to Figure 1.

Table 4. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified.)

Symbol		Parameter	Conditions	Min	Typ	Max	Unit	
INVERTER PART								
V _{CE(SAT)}		Collector – Emitter Saturation Voltage	V _{DD} = V _{BS} = 15 V, V _{IN} = 5 V, I _C = 3 A	T _J = 25°C	–	1.85	2.30	V
				T _J = 150°C	–	2.30	–	V
V _F		FWDi Forward Voltage	V _{IN} = 0 V, I _F = 3 A	T _J = 25°C	–	1.95	2.50	V
				T _J = 150°C	–	1.85	–	V
HS	t _{ON}	Switching Times	V _{PN} = 400 V, V _{DD} = V _{BS} = 15 V, I _C = 4 A, T _J = 25°C V _{IN} = 0 V ↔ 5 V, Inductive load (Note 3)	0.30	0.70	1.10	μs	
	t _{C(ON)}			–	0.15	0.45	μs	
	t _{OFF}			–	0.50	1.00	μs	
	t _{C(OFF)}			–	0.10	0.40	μs	
	t _{rr}			–	0.10	–	μs	
LS	t _{ON}		V _{PN} = 400 V, V _{DD} = V _{BS} = 15 V, I _C = 4 A, T _J = 25°C V _{IN} = 0 V ↔ 5 V, Inductive load (Note 3)	0.30	0.70	1.10	μs	
	t _{C(ON)}			–	0.15	0.45	μs	
	t _{OFF}			–	0.50	1.00	μs	
	t _{C(OFF)}			–	0.10	0.40	μs	
	t _{rr}			–	0.10	–	μs	
I _{CES}		Collector – Emitter Leakage Current	V _{CE} = V _{CES}	–	–	1.00	mA	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. t_{ON} and t_{OFF} include the propagation delay of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching times of IGBT under the given gate-driving condition internally. For the detailed information, please see Figure 3.

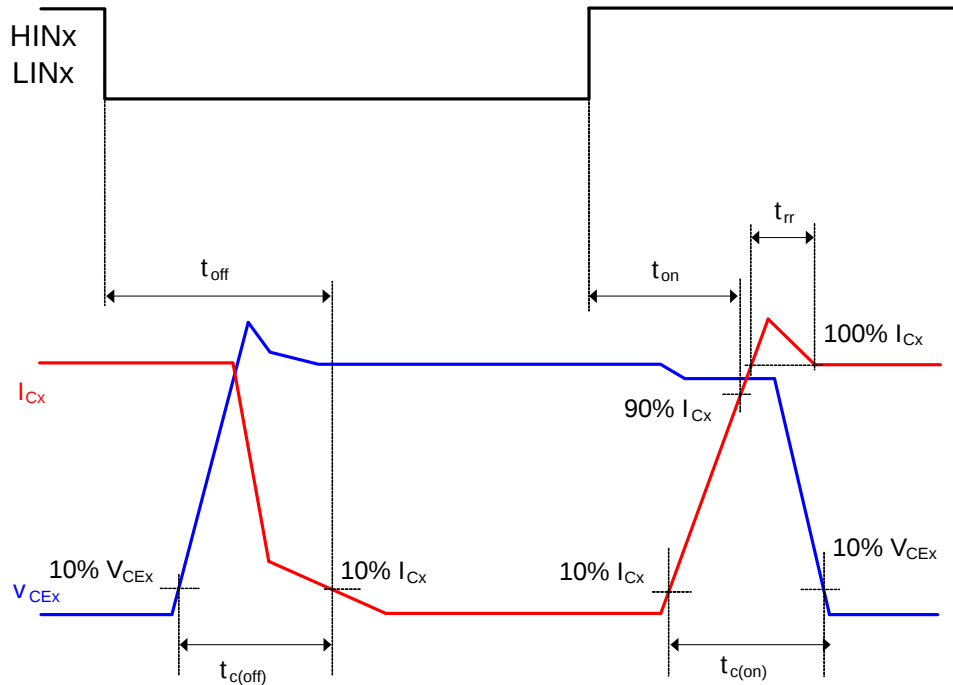


Figure 3. Switching Time

The schematic diagram illustrates the internal structure of the SPM 8 chip, which is a one-leg diagram. The chip includes a high-side MOSFET (HO) and a low-side MOSFET (LO) connected to a common source (VS). The gate of the HO MOSFET is connected to the LIN node, and the gate of the LO MOSFET is connected to the LO node. The drain of the HO MOSFET is connected to the P node, and the drain of the LO MOSFET is connected to the N_{U,V,W} node. The output voltage is labeled V_{U,V,W} and the output current is labeled I_C. The diagram also shows the external components: a 5V input source, a 15V V_{BS} supply, a 15V V_{DD} supply, a 5V V_{LN} supply, a 10kΩ resistor, a 400V output capacitor, and a 400V output inductor. The output voltage is labeled V_{U,V,W} and the output current is labeled I_C.

Figure 10 consists of two side-by-side line graphs showing switching loss E_{sw} in μJ on the y-axis (0 to 200) versus collector current I_c in AMPERES on the x-axis (0.0 to 4.0). Both graphs are for an inductive load with $V_{PN} = 300V$, $V_{DD} = 15V$, and $T_j = 25^\circ C$ (left) and $T_j = 150^\circ C$ (right). The legend for both graphs is: IGBT Turn-on, E_{on} (red line); IGBT Turn-off, E_{off} (blue line); and FRD Turn-off, E_{rec} (green line). The switching loss increases linearly with collector current. At $150^\circ C$, the switching losses are significantly higher than at $25^\circ C$.

I_c [A]	$T_j = 25^\circ C$ (E_{sw} in μJ)			$T_j = 150^\circ C$ (E_{sw} in μJ)		
	E_{on}	E_{off}	E_{rec}	E_{on}	E_{off}	E_{rec}
0.5	15	10	5	20	15	10
1.0	30	20	10	40	30	20
1.5	45	30	15	60	40	30
2.0	60	40	20	80	50	40
2.5	75	50	25	100	60	50
3.0	90	60	30	120	70	60
3.5	105	70	35	140	80	70
4.0	120	80	40	160	90	80

T_{HVIC} [°C]	V_{TS} [V] (3.3V pull-up)	V_{TS} [V] (5V pull-up)
0	3.3	4.8
25	2.9	4.3
50	2.5	3.8
75	2.1	3.3
100	1.7	2.8
125	1.3	2.3
150	1.3	1.3

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Table 5. ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CONTROL PART						
I _{QDD}	Quiescent V _{DD} Supply Current	V _{DD} = 15 V, I _{N(UH,VH,WH,UL,VL,WL)} = 0 V	V _{DD} – COM	–	–	1.7 mA
I _{PDD}	Operating V _{DD} Supply Current	V _{DD} = 15 V, f _{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input	V _{DD} – COM	–	–	1.8 mA
I _{QBS}	Quiescent V _{BS} Supply Current	V _{BS} = 15 V, I _{N(UH, VH, WH)} = 0 V	V _{B(U)} – V _{S(U)} , V _{B(V)} – V _{S(V)} , V _{B(W)} – V _{S(W)}	–	–	100 μA
I _{PBS}	Operating V _{BS} Supply Current	V _{DD} = V _{BS} = 15 V, f _{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for high – side	V _{B(U)} – V _{S(U)} , V _{B(V)} – V _{S(V)} , V _{B(W)} – V _{S(W)}	–	–	300 μA
V _{FOH}	Fault Output Voltage	V _{SC} = 0 V, V _F Circuit: 10 kΩ to 5 V Pull-up	3.81	–	–	V
V _{FOL}		V _{SC} = 1 V, V _F Circuit: 10 kΩ to 5 V Pull-up	–	–	0.5	V
V _{SC(ref)}	Short-Circuit Trip Level	V _{DD} = 15 V (Note 4)	0.46	0.49	0.52	V
UV _{DDD}	Supply Circuit Under-Voltage Protection	Detection level	10.0	11.5	13.0	V
UV _{DDR}		Reset level	10.5	12.0	13.5	V
UV _{BSD}		Detection level	9.5	11.0	12.5	V
UV _{BSR}		Reset level	10.0	11.5	13.0	V
I _{FO_T}	HVIC Temperature Sensing Current	V _{DD} = V _{BS} = 15 V, T _{HVIC} = 25°C	–	82.5	–	μA
		V _{DD} = V _{BS} = 15 V, T _{HVIC} = 75°C	–	207.5	–	μA
V _{FO_T}	HVIC Temperature Sensing Voltage See Figure 7	V _{DD} = V _{BS} = 15 V, T _{HVIC} = 25°C, 10 kΩ to 5 V Pull-up	–	4.18	–	V
		V _{DD} = V _{BS} = 15 V, T _{HVIC} = 75°C, 10 kΩ to 5 V Pull-up	–	2.93	–	V
t _{FOD}	Fault-Out Pulse Width		40	–	–	μs
V _{FSDR}	Shut-down Reset level	Applied between /FO – COM	–	–	2.4	V
V _{FSDD}	Shut-down Detection level		0.8	–	–	V
V _{IN(ON)}	ON Threshold Voltage	Applied between I _{N(UH)} , I _{N(VH)} , I _{N(WH)} , I _{N(UL)} , I _{N(VL)} , I _{N(WL)} – COM	–	–	2.4	V
V _{IN(OFF)}	OFF Threshold Voltage		0.8	–	–	V
BOOTSTRAP DIODE PART						
R _{BS}	Bootstrap Diode Resistance	V _{DD} = 15 V, T _J = 25°C	–	280	–	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Short-circuit current protection function is for all six IGBTs if the /FO, /SD_W, V_{TS} pin is connected to /SD_x pins.

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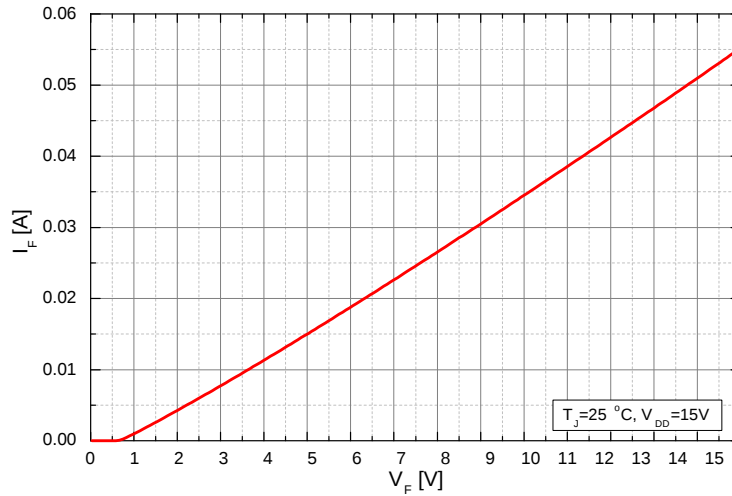


Figure 7. Built-In Bootstrap Diode Characteristics

Table 6. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{PN}	Supply Voltage	Applied between P – N _U , N _V , N _W	–	300	400	V
V _{DD}	Control Supply Voltage	Applied between V _{DD} – COM	14.0	15	16.5	V
V _{BS}	High – Side Bias Voltage	Applied between V _{B_U} – V _{S_U} , V _{B_V} – V _{S_V} , V _{B_W} – V _{S_W}	13.0	15	18.5	V
dV _{DD} / dt, dV _{BS} / dt	Control Supply Variation		–1	–	1	V/μs
t _{dead}	Blanking Time for Preventing Arm – Short	For each input signal	0.5	–	–	μs
V _{SEN}	Voltage for Current Sensing	Applied between N _U , N _V , N _W – COM (Including surge voltage)	–4		4	V
P _{WIN(ON)}	Minimum Input Pulse Width	V _{DD} = V _{BS} = 15 V, I _C ≤ 10 A, Wiring Inductance between N _{U, V, W} and DC Link N < 10nH (Note 5)	0.7	–	–	μs
P _{WIN(OFF)}			0.7	–	–	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. This product might not make response if input pulse width is less than the recommended value.

Table 7. MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Conditions		Value			Unit
			Min	Typ	Max	
Device Flatness	See Figure 8		0	–	+120	μm
Mounting Torque	Mounting Screw: M3 See Figure 9 (Note 6, 7)	Recommended 0.62 N • m	0.51	0.62	0.72	N • m
Weight			–	15.00	–	g

6. Do not make over torque when mounting screws. Much mounting torque may cause package cracks, as well as bolts and Al heat-sink destruction.

7. Avoid one side tightening stress. Figure 9 shows the recommended torque order for mounting screws. Uneven mounting can cause the DBC substrate of package to be damaged. The pre-screwing torque is set to 20 ~ 30% of maximum torque rating.

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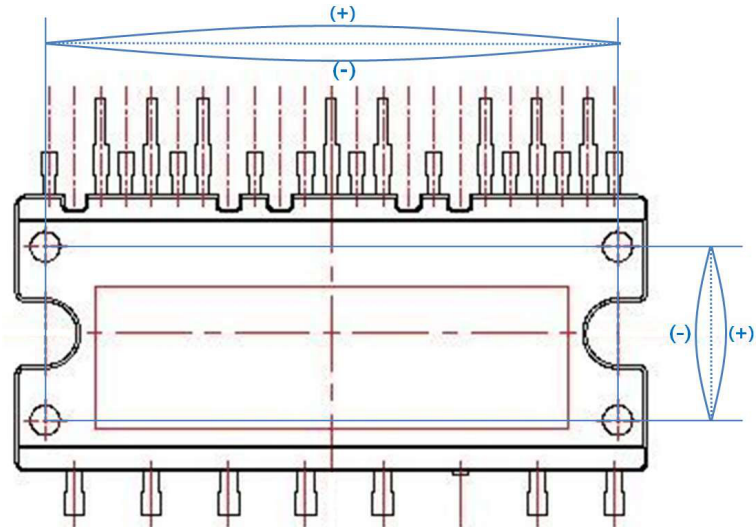


Figure 8. Flatness Measurement Position

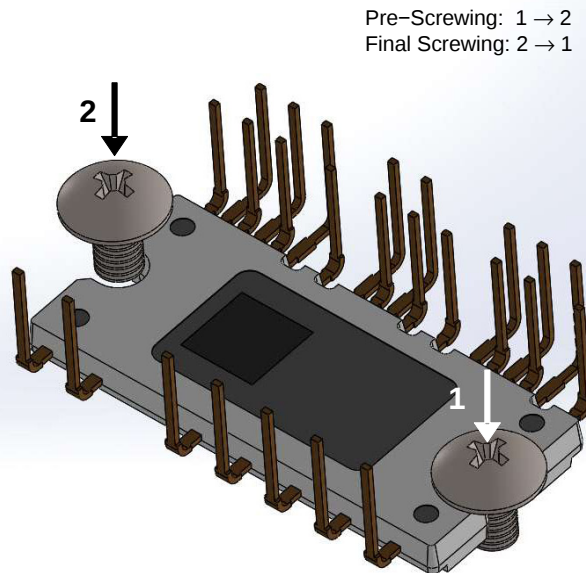
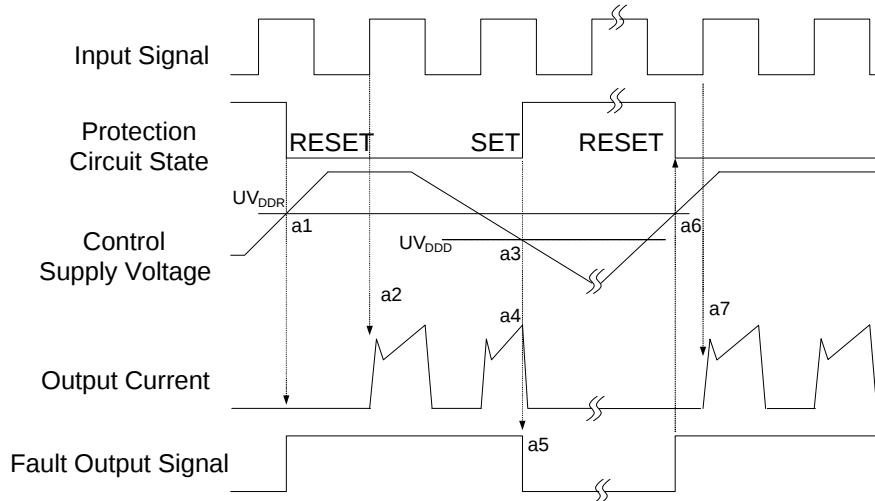


Figure 9. Mounting Screws Torque Order

PACKAGE MARKING AND ORDERING INFORMATION

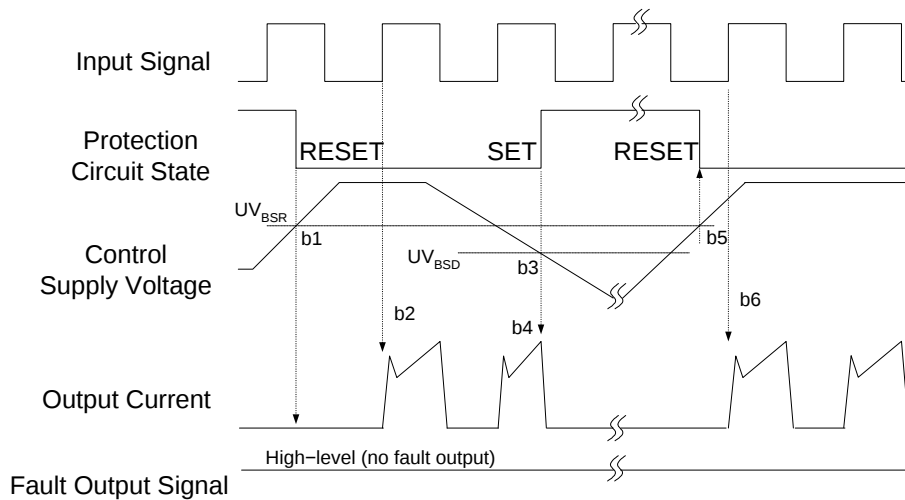
Device	Device Marking	Package	Shipping
FNB80460T3	NB80460T3	SPMFA-A25	15 Units / Rail

TIME CHARTS OF PROTECTIVE FUNCTION



- a1: Control supply voltage rises: after the voltage rises UV_{DD} , the circuits start to operate when next input is applied.
 a2: Normal operation: IGBT ON and carrying current.
 a3: Under-voltage detection (UV_{DD}).
 a4: IGBT OFF in spite of control input condition.
 a5: Fault output operation starts.
 a6: Under-voltage reset (UV_{DD}).
 a7: Normal operation: IGBT ON and carrying current.

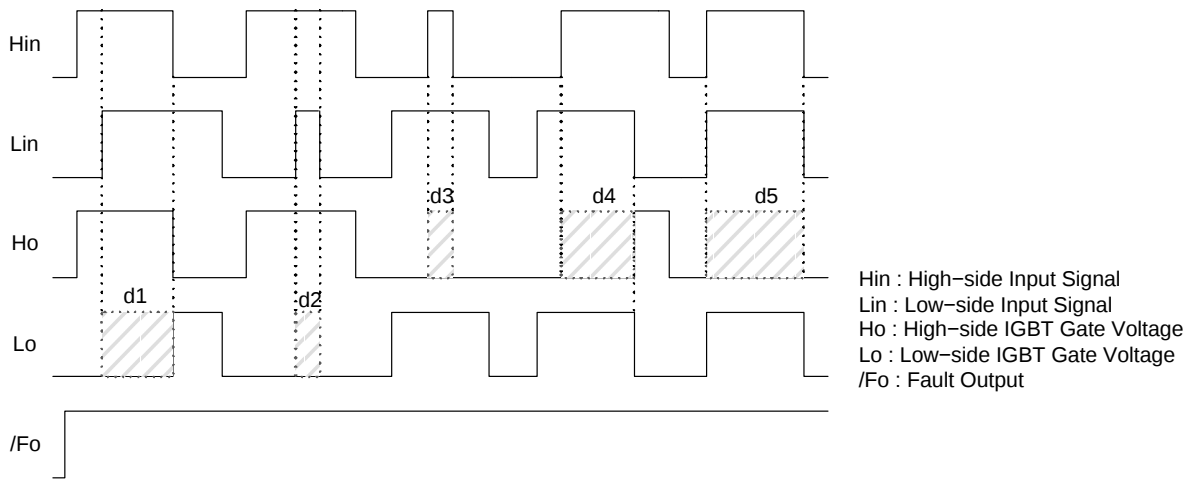
Figure 10. Under-Voltage Protection (Low-Side)



- b1: Control supply voltage rises: after the voltage reaches UV_{BSR} , the circuits start to operate when next input is applied.
 b2: Normal operation: IGBT ON and carrying current.
 b3: Under-voltage detection (UV_{BSD}).
 b4: IGBT OFF in spite of control input condition, but there is no fault output signal.
 b5: Under-voltage reset (UV_{BSR}).
 b6: Normal operation: IGBT ON and carrying current.

Figure 11. Under-Voltage Protection (High-Side)

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- d1: High Side First – Input – First – Output Mode
- d2: Low Side Noise Mode: No LO
- d3: High Side Noise Mode: No HO
- d4: Low Side First – Input – First – Output Mode
- d5: IN – Phase Mode: No HO

Figure 12. Inter-Lock Function

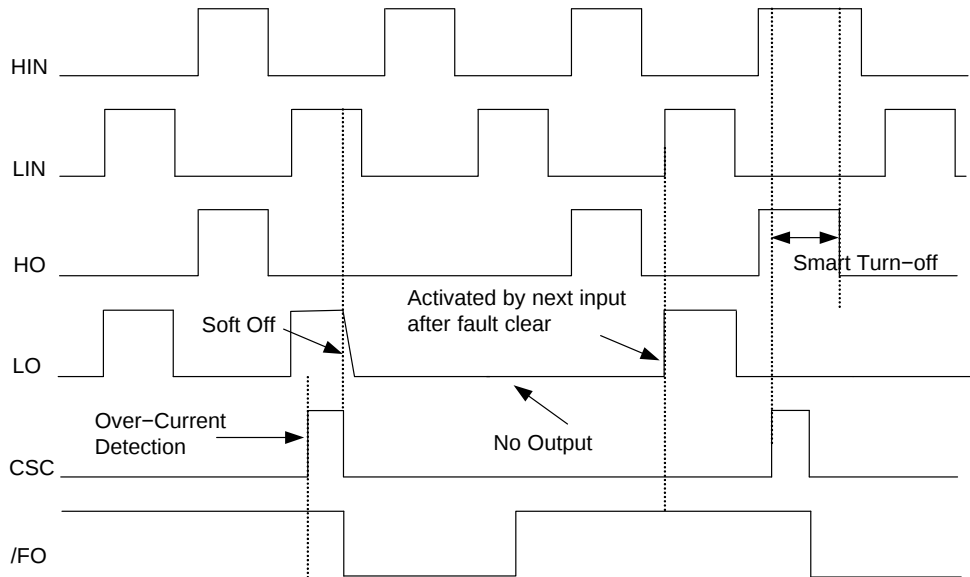
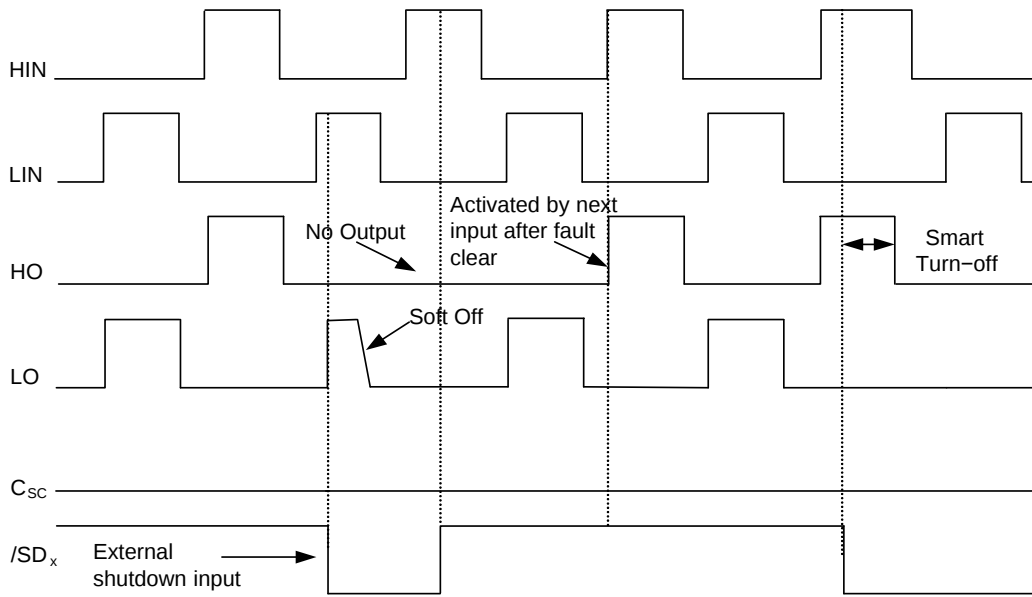


Figure 13. Fault-Out Function by Over Current Protection

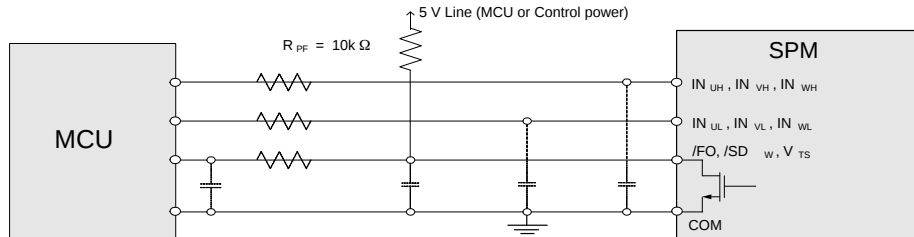
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HIN : High-side Input Signal
 LIN : Low-side Input Signal
 HO : High-Side Output Signal
 LO : Low-Side Output Signal
 CSC : Over Current Detection Input
 /SD_x : Shutdown Input Function

Figure 14. Shutdown Input Function by External Command

INPUT/OUTPUT INTERFACE CIRCUIT



NOTE: RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the SPM 8 product integrates 5 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

Figure 15. Recommended MCU I/O Interface Circuit

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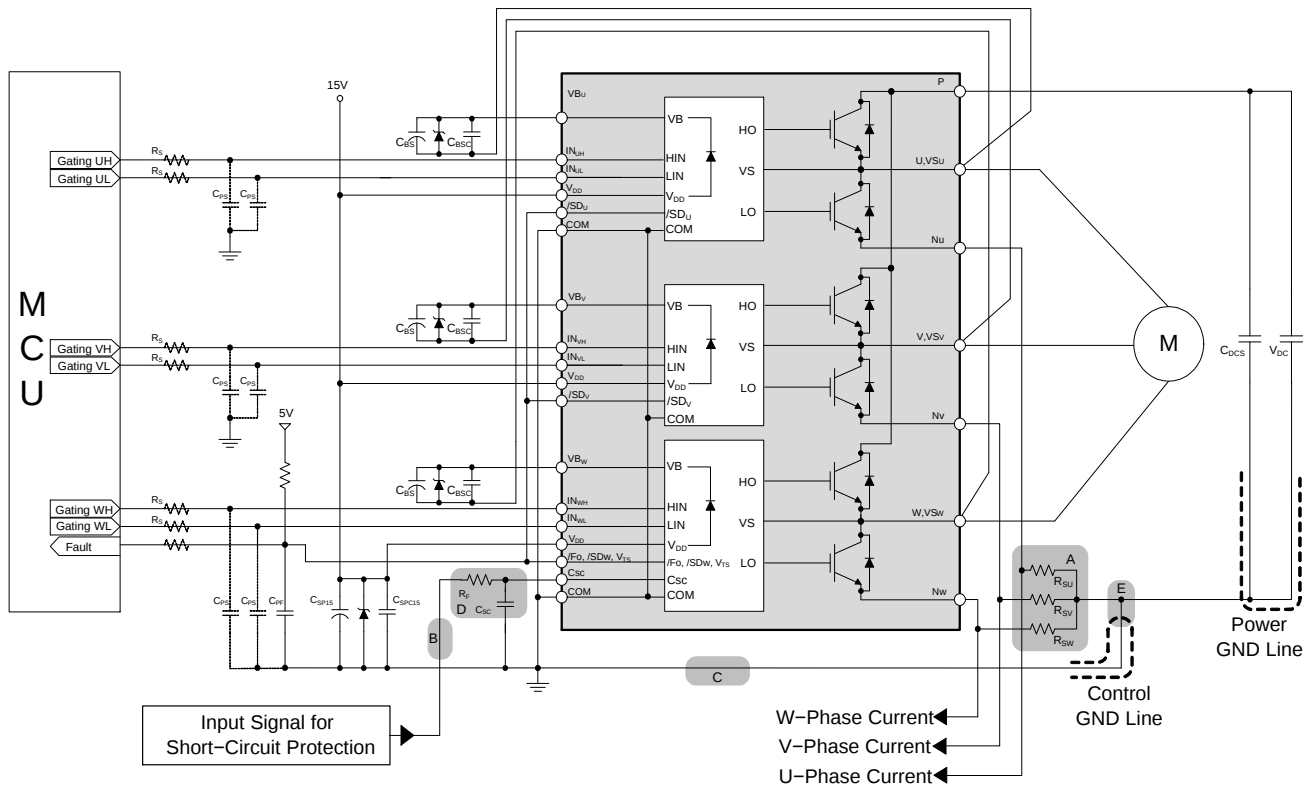


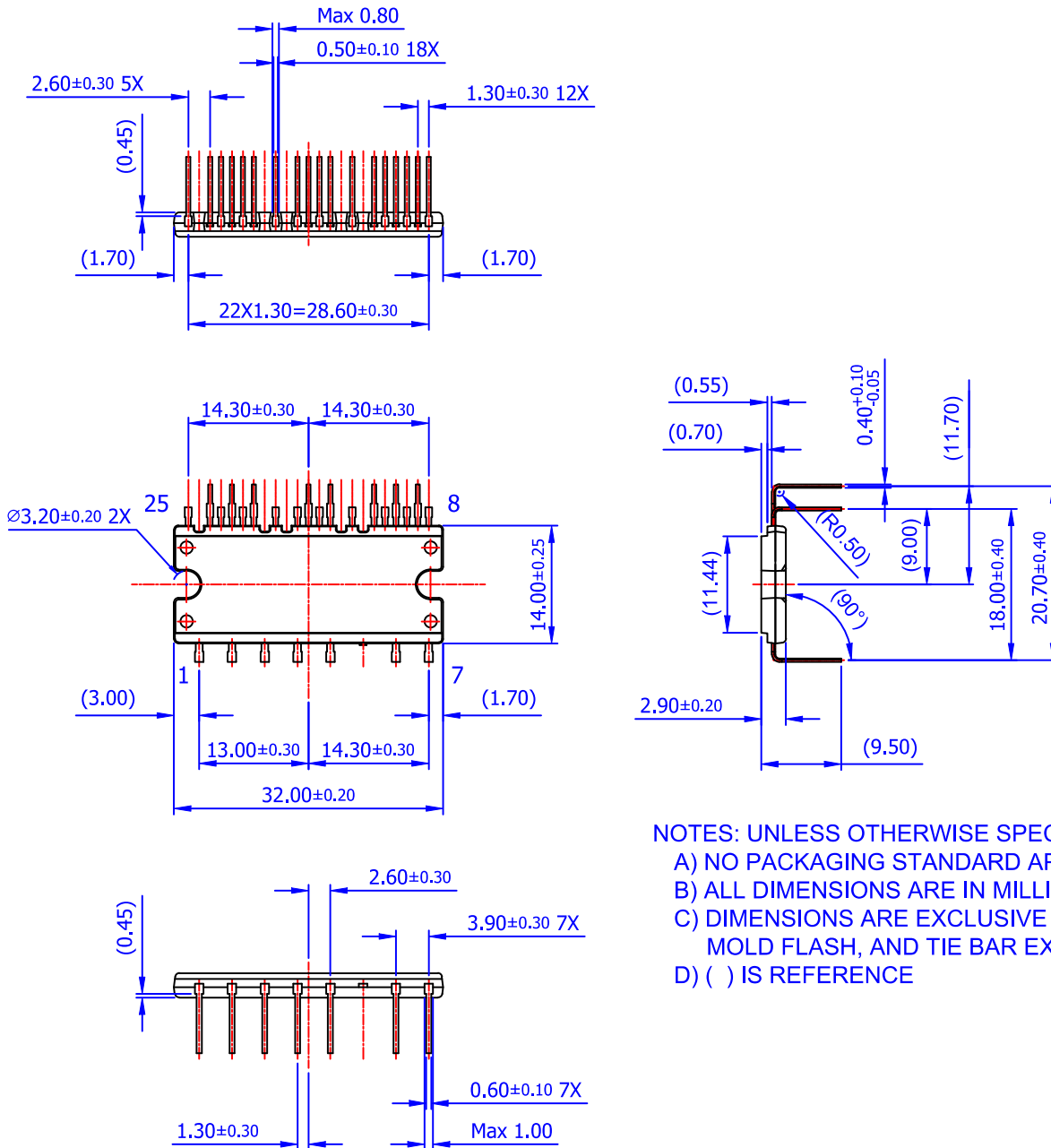
Figure 16. Typical Application Circuit

NOTES:

8. To avoid malfunction, the wiring of each input should be as short as possible (Less than 2 ~ 3 cm).
9. /FO is open-drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I_{FO} up to 2 mA. (Figure 15.)
10. C_{SP15} of around seven times larger than bootstrap capacitor C_{BS} is recommended.
11. Input signal is active-HIGH type. There is a 5 k Ω resistor inside the IC to pull down each input signal line to GND. RC coupling circuits are recommended for the prevention of input signal oscillation. $R_S C_{PS}$ time constant should be selected in the range 50 ~ 150 ns (Recommended $R_S = 100 \Omega$, $C_{PS} = 1$ nF).
12. Each wiring pattern inductance of A point should be minimized (Recommend less than 10nH). Use the shunt resistor $R_{S(U/V/W)}$ of surface mounted (SMD) type to reduce wiring inductance. To prevent malfunction, wiring of point E should be connected to the terminal of the shunt resistor $R_{S(U/V/W)}$ as close as possible.
13. To prevent errors of the protection function, the wiring of B, C, and D point should be as short as possible.
14. In the short-circuit current protection circuit, please select the $R_F C_{SC}$ time constant in the range 1.5 ~ 2 μ s. Do enough evaluation on the real system because short-circuit protection time may vary wiring pattern layout and value of the R_F and C_{SC} time constant.
15. The connection between control GND line and power GND line which includes the N_U , N_V , N_W must be connected to only one point. Please do not connect the control GND to the power GND by the broad pattern. Also, the wiring distance between control GND and power GND should be as short as possible.
16. Each capacitor should be mounted as close to the pins of the Motion SPM 8 product as possible.
17. To prevent surge destruction, the wiring between the smoothing capacitor and the P and GND pins should be as short as possible. The use of a high frequency non-inductive capacitor of around 0.1 ~ 0.22 μ F between the P and GND pins is recommended.
18. Relays are used in almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the CPU and the relays.
19. The zener diode or transient voltage suppressor should be adapted for the protection of ICs from the surge destruction between each pair of control supply terminals (Recommended zener diode is 22 V / 1 W, which has the lower zener impedance characteristic than about 15 Ω).
20. Please choose the electrolytic capacitor with good temperature characteristic in C_{BS} . Also, choose 0.1 ~ 0.2 μ F R-category ceramic capacitors with good temperature and frequency characteristics in C_{BSC} .
21. For the detailed information, please refer to the application notes.
22. /FO and /SD must be connected as short as possible.

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